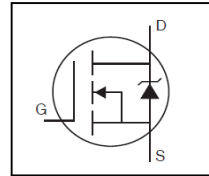


- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET



$V_{DSS}$	<b>55V</b>
$R_{DS(on)}$	<b>0.04Ω</b>
$I_D$	<b>21A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Description**

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Full Pak eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heat sink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heat sink using a single clip or by a single screw fixing.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFIZ34NPbF	TO-220 Full-Pak	Tube	50	IRFIZ34NPbF

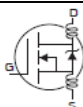
**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	21	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	15	
$I_{DM}$	Pulsed Drain Current ①⑥	100	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	37	W
	Linear Derating Factor	0.24	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ②⑥	110	mJ
$I_{AR}$	Avalanche Current ①⑥	16	A
$E_{AR}$	Repetitive Avalanche Energy ①	3.7	mJ
dv/dt	Peak Diode Recovery dv/dt③⑥	5.0	V/ns
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
$T_{STG}$			
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

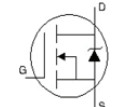
**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	4.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

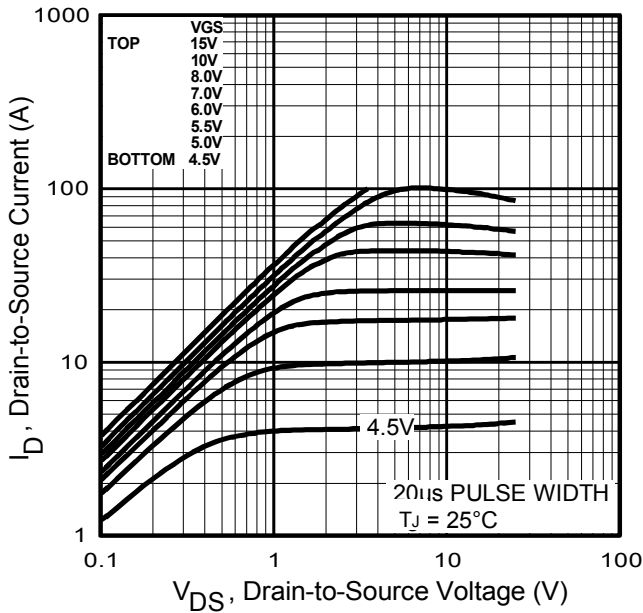
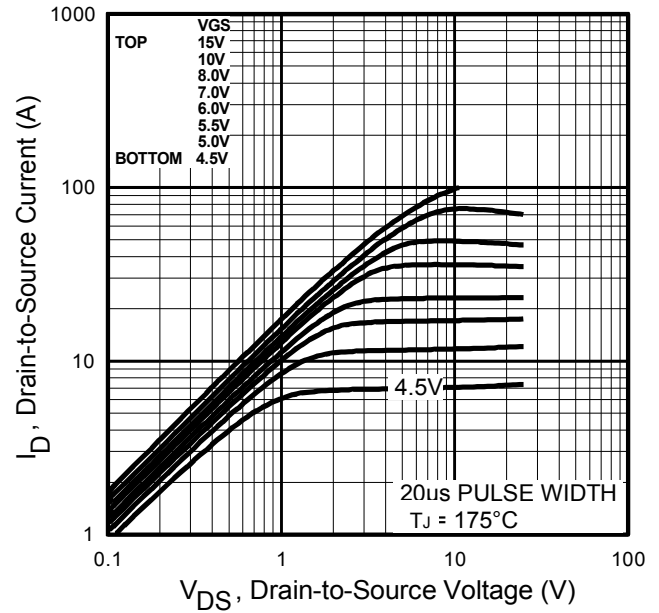
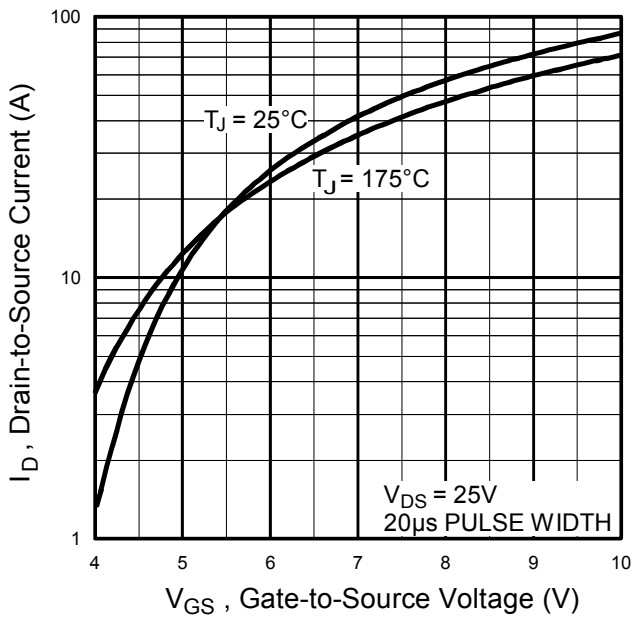
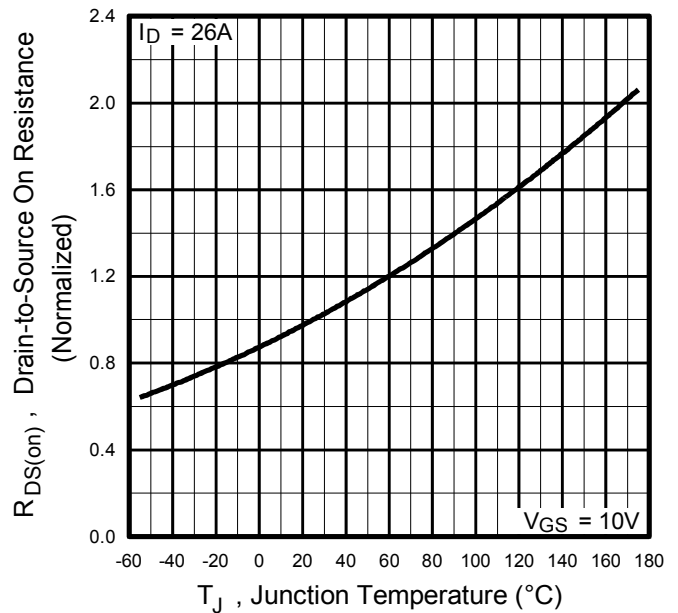
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.052	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA ⑥
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.04	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Trans conductance	6.5	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 16A⑥
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	34	nC	I <sub>D</sub> = 16A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	6.8		V <sub>DS</sub> = 44V
Q <sub>gd</sub>	Gate-to-Drain Charge	—	—	14		V <sub>GS</sub> = 10V, See Fig. 6 and 13④⑥
t <sub>d(on)</sub>	Turn-On Delay Time	—	7.0	—	ns	V <sub>DD</sub> = 26V
t <sub>r</sub>	Rise Time	—	49	—		I <sub>D</sub> = 16A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	31	—		R <sub>G</sub> = 18Ω
t <sub>f</sub>	Fall Time	—	40	—		R <sub>D</sub> = 1.8Ω, See Fig. 10④⑥
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	700	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	240	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	100	—		f = 1.0MHz, See Fig. 5⑥
C	Drain to Sink Capacitance	—	12	—		f = 1.0MHz

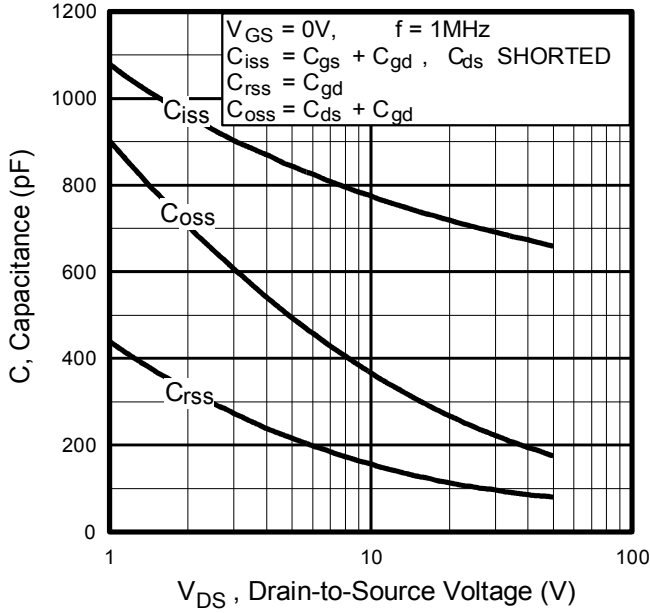
**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	21	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	100		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.6	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 11A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	57	86	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 16A
Q <sub>rr</sub>	Reverse Recovery Charge	—	130	200	μC	di/dt = 100A/μs ④⑥
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

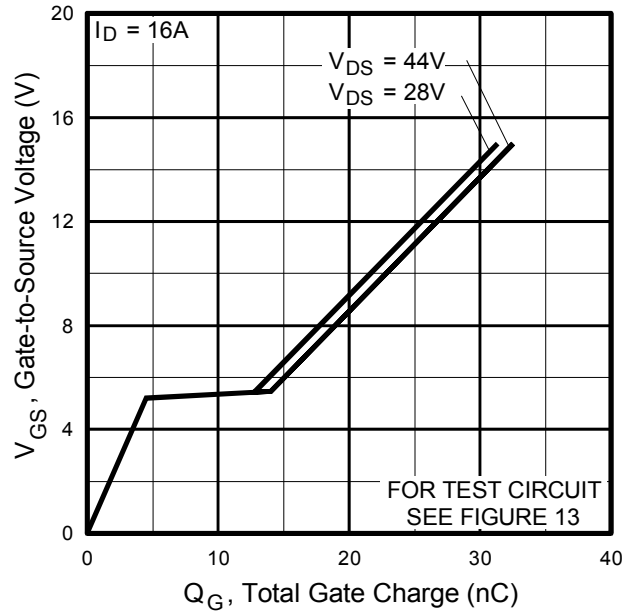
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V<sub>DD</sub> = 25V, starting T<sub>J</sub> = 25°C, L = 610μH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 16A (See fig. 12)
- ③ I<sub>SD</sub> ≤ 16A, di/dt ≤ 420A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ t = 60s, f = 60Hz
- ⑥ Uses IRFZ34N data and test conditions.

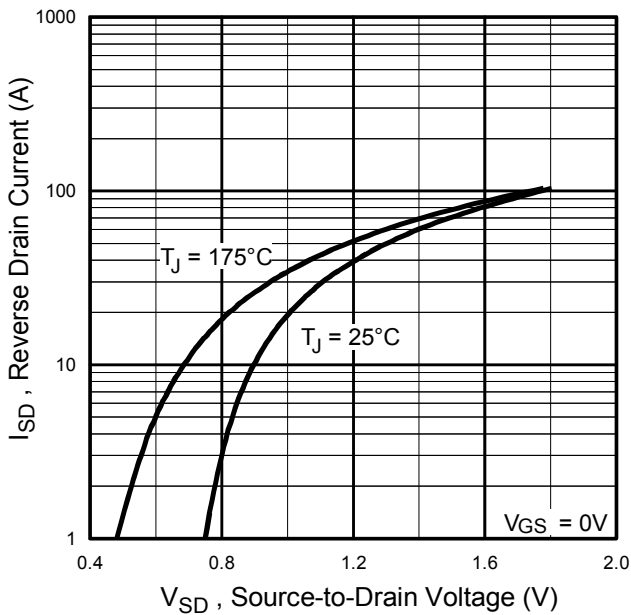

**Fig. 1** Typical Output Characteristics

**Fig. 2** Typical Output Characteristics

**Fig. 3** Typical Transfer Characteristics

**Fig. 4** Normalized On-Resistance vs. Temperature



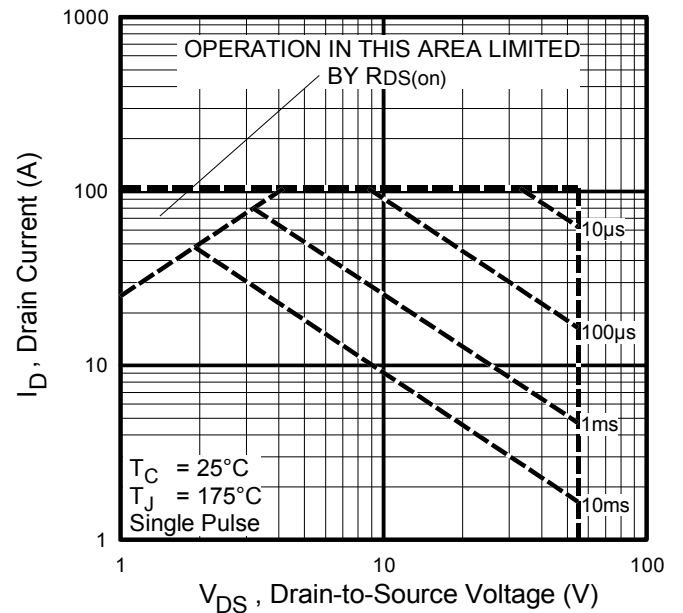
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



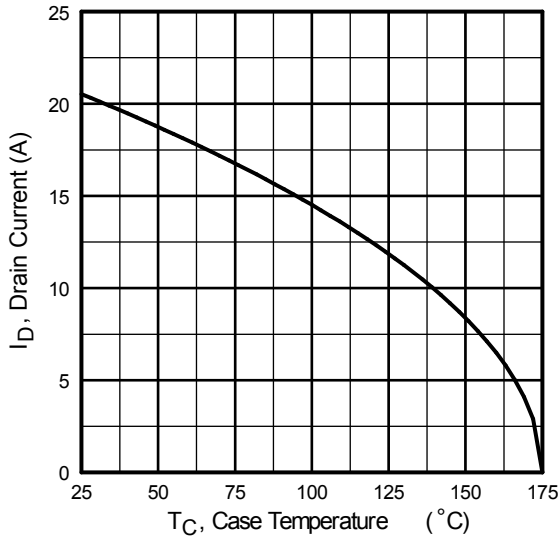
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

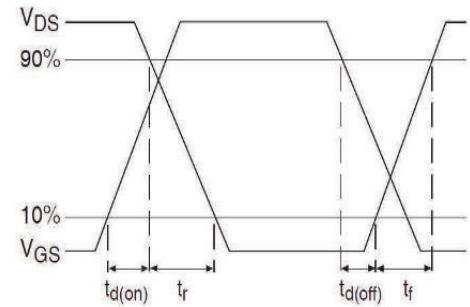
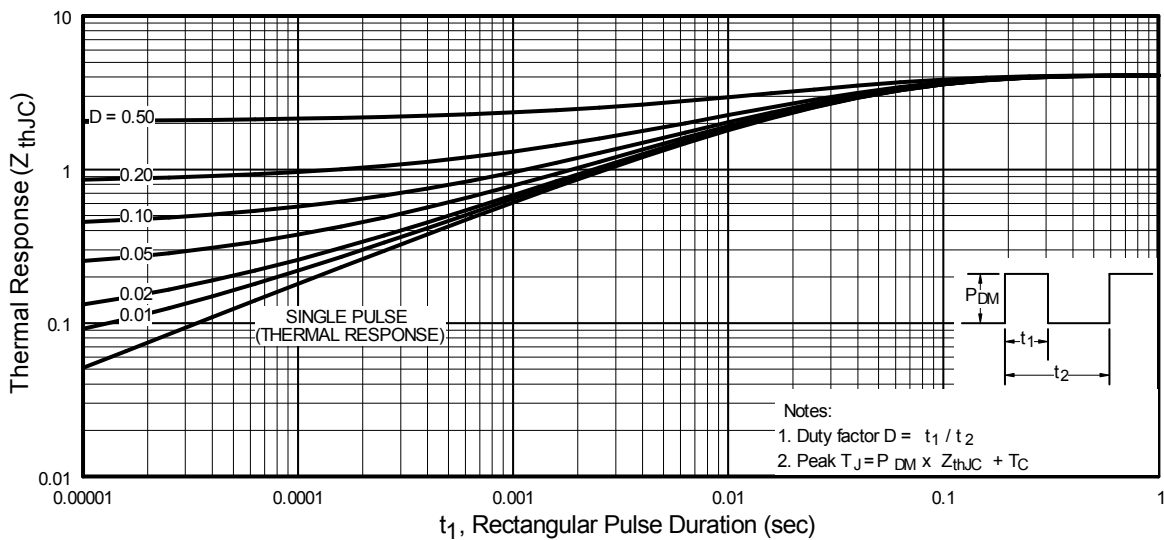


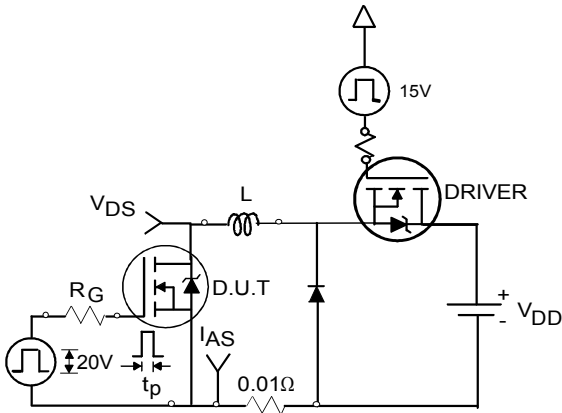
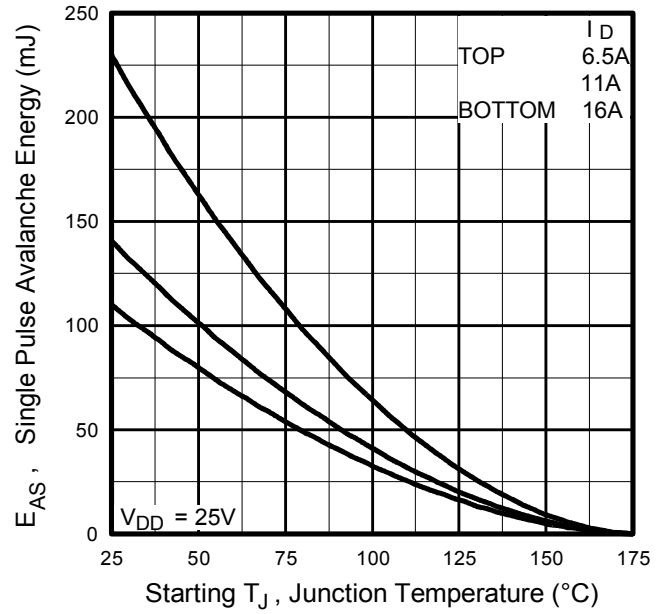
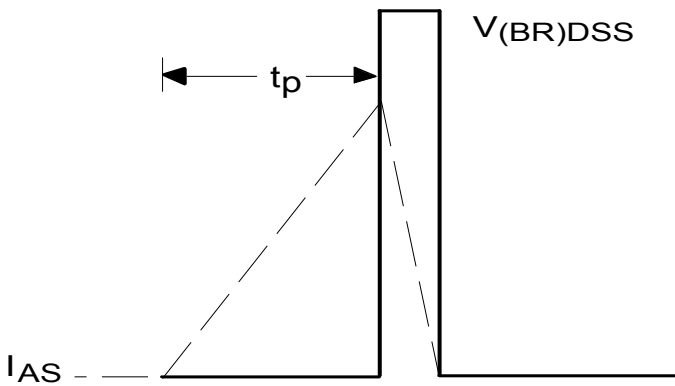
**Fig 7** Typical Source-to-Drain Diode Forward Voltage

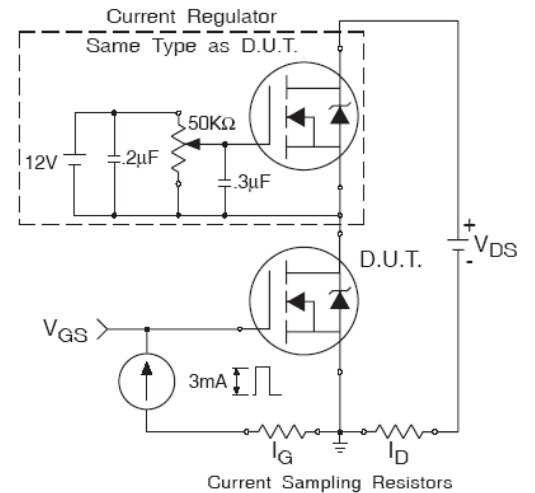


**Fig 8.** Maximum Safe Operating Area

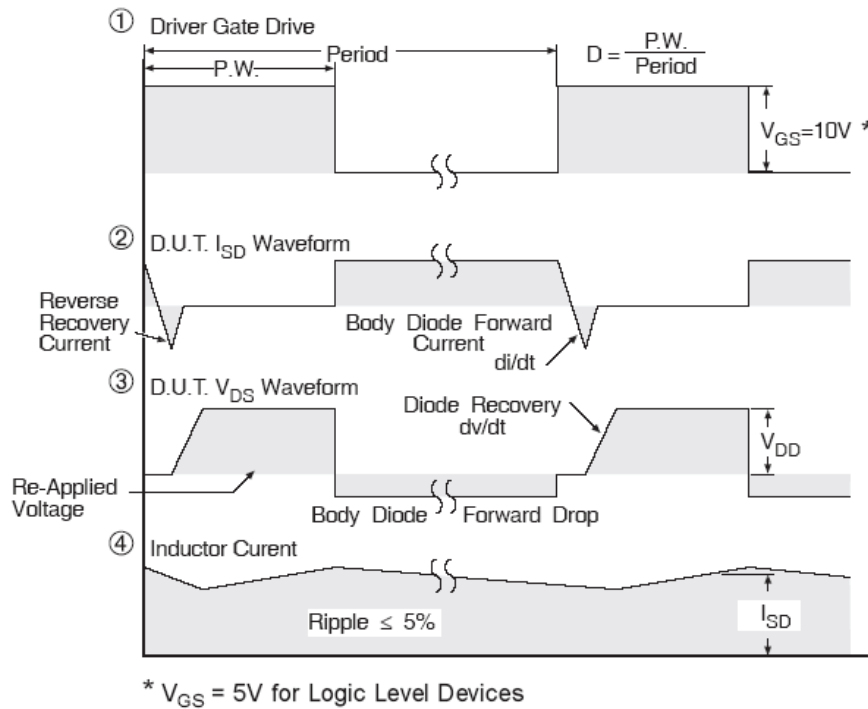

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10a.** Switching Time Test Circuit

**Fig 10b.** Switching Time Waveforms

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

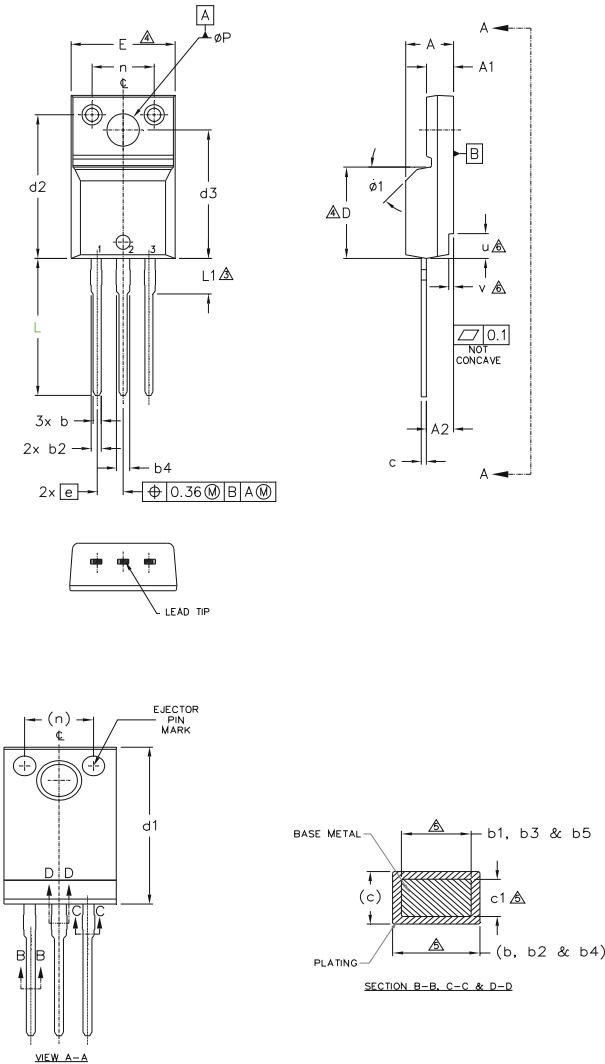

**Fig 12a. Unclamped Inductive Test Circuit**

**Fig 12c. Maximum Avalanche Energy vs. Drain Current**

**Fig 12b. Unclamped Inductive Waveforms**

**Fig 13a. Gate Charge Waveform**

**Fig 13b. Gate Charge Test Circuit**

### Peak Diode Recovery dv/dt Test Circuit



**Fig 14.** Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs

**TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))**


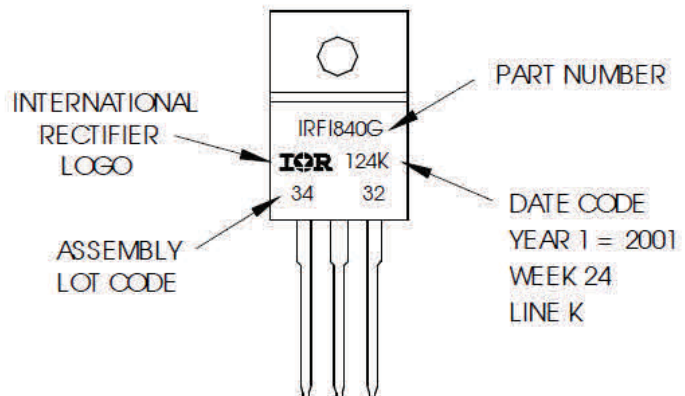
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
  - 5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
  - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
  - 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.57	4.83	.180	.190	LEAD ASSIGNMENTS  HEXFET 1.- GATE 2.- DRAIN 3.- SOURCE	
A1	2.57	2.82	.101	.111		
A2	2.51	2.92	.099	.115		
b	0.61	0.94	.024	.037		
b1	0.61	0.89	.024	.035		5
b2	0.76	1.27	.030	.050		5
b3	0.76	1.22	.030	.048		5
b4	1.02	1.52	.040	.060		5
b5	1.02	1.47	.040	.058		5
c	0.33	0.63	.013	.025		5
c1	0.33	0.58	.013	.023	5	
D	8.66	9.80	.341	.386	4	
d1	15.80	16.13	.622	.635	IGBTs, CoPACK 1.- GATE 2.- COLLECTOR 3.- EMITTER	
d2	13.97	14.22	.550	.560		
d3	12.29	12.93	.484	.509		
E	9.63	10.74	.379	.423		
e	2.54 BSC		.100 BSC			
L	13.21	13.72	.520	.540	3	
L1	3.10	3.68	.122	.145		
n	6.05	6.60	.238	.260	6	
øP	3.05	3.45	.120	.136		
u	2.39	2.49	.094	.098		
v	0.41	0.51	.016	.020		
ø1	-	45°	-	45°		

**TO-220 Full-Pak Part Marking Information**

EXAMPLE: THIS IS AN IRFI840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW24, 2001  
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position  
indicates "Lead-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to website at <http://www.irf.com/package/>



**Qualification Information**

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F) †	
<b>Moisture Sensitivity Level</b>	TO-220 Full-Pak	N/A
<b>RoHS Compliant</b>	Yes	

† Applicable version of JEDEC standard at the time of product release.

**Revision History**

Date	Comments
04/27/2017	<ul style="list-style-type: none"> <li>Changed datasheet with Infineon logo - all pages.</li> <li>Corrected Package Outline on page 8.</li> <li>Added disclaimer on last page.</li> </ul>

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